

L Number	Hits	Search Text	DB	Time stamp
7	92	@ad<=20010323 and 'epi' and 'silicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/26 11:54
8	9	@ad<=20010323 and 'epitaxial silicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/26 11:10
9	1	("6528363").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/26 11:10
24	7	@ad<=20010323 and 'conductor' same 'epi' same 'polysilicon' same 'amorphous'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/26 12:04
25	0	@ad<=20010323 and 'conductive' same 'epi' same 'polysilicon' same 'amorphous'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/26 12:04
-	10	(("5393681") or ("6391692") or ("5308782") or ("5998248") or ("6319782")).PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/25 13:55
-	162	257/929 and @ad<=20010323	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/25 14:15
-	542	438/300 and @ad<=20010323	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 08:38
-	4	@ad<=20010323 and 'raised vertical lateral transistor'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/04 16:02
-	1	@ad<=20010323 and 'raised source and drain'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/04 15:26
-	1	@ad<=20010323 and 'epitaxial' and 'source or drain'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/04 15:30
-	8	@ad<=20010323 and 'epitaxial' and 'source and drain'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/04 15:30
-	3470	gardner.inv.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/04 15:45
-	6	gardner.inv. and 'vertical transistor' and @ad<=20010323	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/04 15:48

	4	@ad<=20010323 and 'elevated source and drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:24
	257	@ad<=20010323 and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/04 16:06
	37	@ad<=20010323 and 'epitaxial' with 'elevated source'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 08:56
	1	"4728623".PN.	USPAT	2002/09/04 16:31
	1	"4738937".PN.	USPAT	2002/09/04 16:31
	1	"4918029".PN.	USPAT	2002/09/04 16:31
	1	"5004702".PN.	USPAT	2002/09/04 16:31
	1	"5030583".PN.	USPAT	2002/09/04 16:31
	1	"5032538".PN.	USPAT	2002/09/04 16:31
	1	"5045494".PN.	USPAT	2002/09/04 16:31
	1	"5272109".PN.	USPAT	2002/09/04 16:31
	1	"5496750".PN.	USPAT	2002/09/04 16:32
	1	"5378651".PN.	USPAT	2002/09/04 16:38
	1	"5321306".PN.	USPAT	2002/09/04 16:38
	1	"5296388".PN.	USPAT	2002/09/04 16:38
	1	"5250454".PN.	USPAT	2002/09/04 16:38
	1	"5213991".PN.	USPAT	2002/09/04 16:39
	1	"5079180".PN.	USPAT	2002/09/04 16:39
	1	"5057899".PN.	USPAT	2002/09/04 16:39
	1	"4966861".PN.	USPAT	2002/09/04 16:39
	1	"4814841".PN.	USPAT	2002/09/04 16:41
	1	"5057893".PN.	USPAT	2002/09/04 16:48
	18	((("6096596") or ("6090691") or ("6057200") or ("6001697") or ("5998844") or ("5963822") or ("5945698") or ("5933738") or ("5863826")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/05 08:23
	18	((("5831334") or ("5677573") or ("5641694") or ("5600161") or ("5497017") or ("5312768") or ("5156987") or ("5122476") or ("5087586")).PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/05 10:18
	2	("5308782").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/05 10:19
	2	("6319782").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/05 10:19
	1731	((438/300) or (257/302) or (257/929) or (257/592)).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 08:44
	12	ri-seiko.in.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 08:44
	38	@ad<=20010323 and 'epitaxial' with 'elevated source'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:33

	263	@ad<=20010323 and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 09:33
	263	@ad<=20010323 and elevated adj1 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 09:02
	95	@ad<=20010323 and elevated adj1 drain	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 09:02
	112	@ad<=20010323 and raised adj1 drain	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 09:03
	229	@ad<=20010323 and raised adj1 source	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 09:03
	0	@ad<=20010323 and 'epitaxial silicon gate' with 'elevated source'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 09:38
	20	@ad<=20010323 and 'silicon gate' and 'elevated source'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 09:38
	47	@ad<=20010323 and 'polysilicon gate' and 'elevated source'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/25 14:14
	0	@ad<=20010323 and 'epitaxial polysilicon gate' and 'elevated source'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/25 14:25
	1	@ad<=20010323 and 'epitaxial polysilicon' and 'elevated source'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 10:08
	56	@ad<=20010323 and 'epitaxial polysilicon'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/21 08:20
	0	@ad<=20010323 and 'epitaxial polysilicon gate'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 14:05
	24	@ad<=20010323 and 'epitaxial gate'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20 14:05
	24	@ad<=20010323 and 'epitaxial gate'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/21 08:30

	560	@ad<=20010323 and polysilicon with epitaxial with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 16:16
	2348	@ad<=20010323 and 'multilayer' same 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:55
	260	(@ad<=20010323 and 'multilayer' same 'gate') and 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 16:18
	0	@ad<=20010323 and 'multilayer gate' with 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 16:33
	1	@ad<=20010323 and epitaxial near grow near polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:20
	693	@ad<=20010323 and 'epitaxial silicon' same 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:32
	367	@ad<=20010323 and 'epitaxial silicon' with 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:41
	9	@ad<=20010323 and 'epitaxial silicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 10:14
	1	@ad<=20010323 and 'multilayer silicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:56
	1	("6534809").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 13:55
	564	@ad<=20010323 and 'polysilicon gate' same 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:18
	390	(257/756).ccls and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:16
	214	@ad<=20010323 and 'floating gate' same 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:18
	2141	@ad<=20010323 and 'elevated' same 'source' and 'drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:28

	413	@ad<=20010323 and 'elevated' with 'source' with 'drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 14:28
	6	@ad<=20010323 and 'epi silicon' and 'elevated' same 'source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 11:54
	1 32	"4074300".PN. @ad<=20010323 and 'gate stack' and 'elevated' same 'source'	USPAT USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 14:37 2003/03/25 15:13
	8	(("4583105") or ("6083815") or ("5885877") or ("5986328")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 15:39
	2	("5198378").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 15:39